# **HYBRID GATE DRIVER IC FOR IGBT**

# **GH-038**

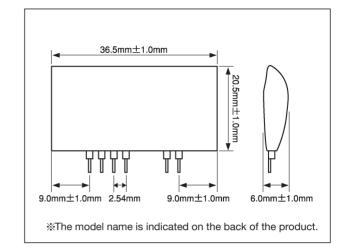






#### SanRex Hybrid Gate Driver IC for IGBT

- High Voltage isolation by Photo Coupler
- Enable to drive IGBT up to dual 300A module
- Operate with single power source
- Support to high-density system design
- Built-in opto coupler input resistor (330 Ω)

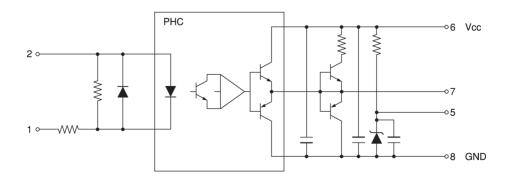


■Maximum Ratings

(Unless otherwise Tj=25°C)

Symbol	Item	Conditions	Ratings			Unit
			Min.	Тур.	Max.	Oille
Vcc	Supply Voltage		23.0	26.0	28.0	V
Vон	Forward Bias Output Voltage	Vcc=26.0V	16.0	18.0	19.0	V
VRB	Reverse Bias Supply Voltage	Vcc=26.0V	7.0	8.0	9.0	V
VFIN	Photo Coupler Input Voltage			5.0	7.0	V
lF	Photo Coupler Input Current	V <sub>FIN</sub> =5.0V	9.0	10.6	12.2	mA
lg1	Output Forward Current	PW=2 $\mu$ s, Dutycycle < 0.05		4.0	6.0	Α
lg2	Output Reverse Current	PW=2 μs, Dutycycle < 0.05		4.0	6.0	Α
tplh	Switching Time-High side	Vcc=26.0V, IF=10mA			1.5	μs
<b>t</b> PHL	Switching Time-Low side	Vcc=26.0V, IF=10mA			1.5	μs
tr	Rise Time	Vcc=26.0V, IF=10mA			1.0	μs
tf	Fall Time	Vcc=26.0V, IF=10mA			1.0	μS
dv/dt	Common Mode Transient immunity		5k	10k		V/μs
Visc	Input /Output Isolation Voltage	AC50/60Hz, 1minute	AC2500			V
Topr	Operational Ambient Temperature		<b>−</b> 25~+80			°C
Tstg	Storage Temperature		<b>−</b> 40∼ <b>+</b> 125			°C

## **Equivalent Circuit**

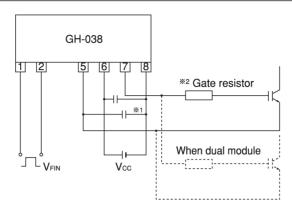








## **■**Examble of Application



- %1 To assure required voltage the capacitor (>10  $\mu$ F) hase to be connected as close to the Driver IC as possible.
- For the value of gate resistor, the resistance value described in IGBT Module specification is recommended. The gate resistance should be determined at less than 6A of peak output current judging from signal delay time and surge voltage.

